

**isc Silicon NPN Power Transistor**
**BU326S**
**DESCRIPTION**

- Collector-Emitter Sustaining Voltage-  
:  $V_{CE(SUS)} = 400V(\text{Min})$
- Low Collector-Emitter Saturation Voltage-  
:  $V_{CE(sat)} = 1.5V(\text{Max.}) @ I_C = 2.5A$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

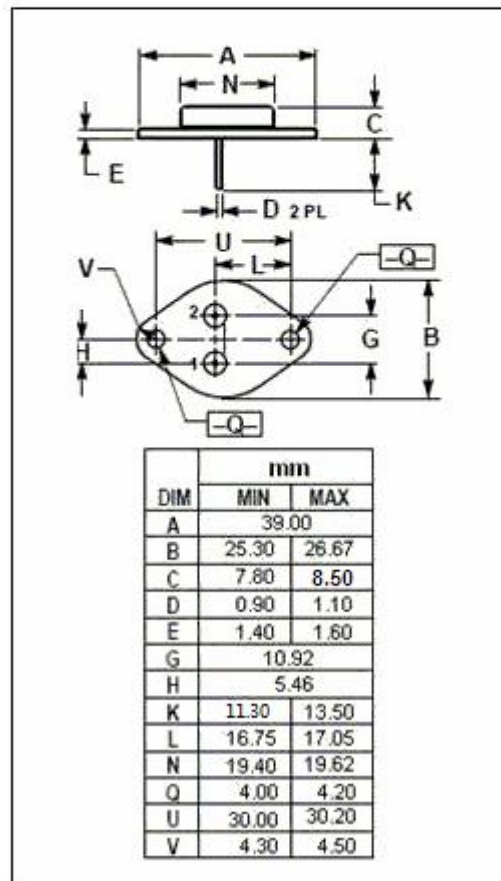
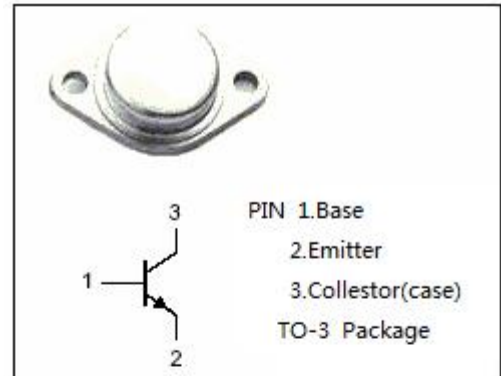
- Designed for use in operating in color TV receivers chopper supplies.

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	800	V
$V_{CEO}$	Collector-Emitter Voltage	400	V
$V_{EBO}$	Emitter-Base Voltage	10	V
$I_C$	Collector Current-Continuous	6	A
$I_{CM}$	Collector Current-Peak	8	A
$I_B$	Base Current-Continuous	3	A
$P_C$	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	75	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-65~150	$^\circ\text{C}$

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	2.33	$^\circ\text{C/W}$



**ELECTRICAL CHARACTERISTICS**

 T<sub>C</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	400			V
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2.5A; I <sub>B</sub> = 0.5A			1.5	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 1.25A			3.0	V
V <sub>BE(sat)-1</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 2.5A; I <sub>B</sub> = 0.5A			1.4	V
V <sub>BE(sat)-2</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 1.25A			1.6	V
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> =800V; V <sub>BE</sub> = 0			1.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 10V; I <sub>C</sub> = 0			1.0	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V		25		
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.2A; V <sub>CE</sub> = 10V, f= 1.0MHz	4			MHz

**Switching Times**

t <sub>on</sub>	Turn-On Time				0.5	μs
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = 2.5A; I <sub>B1</sub> = 0.5A; I <sub>B2</sub> = -1A; V <sub>CC</sub> = 250V			3.5	μs
t <sub>f</sub>	Fall Time				0.5	μs

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